

ABSTRACT

[0093] Embodiments of the invention provide a method of forming a pixel cell and the resultant pixel cell a photo-conversion device formed at a surface of a substrate and a transistor adjacent to the photo-conversion device. The transistor comprises a gate overlying a channel region. The gate comprises at least one gate region having a work-function greater than a work-function of n+ polysilicon. The channel region comprises respective portions below each gate region. A dopant concentration in at least one portion of the channel region is determined at least in part by the work-function of the respective gate region.